

Silicon NPN Power Transistors

2SC2749

DESCRIPTION

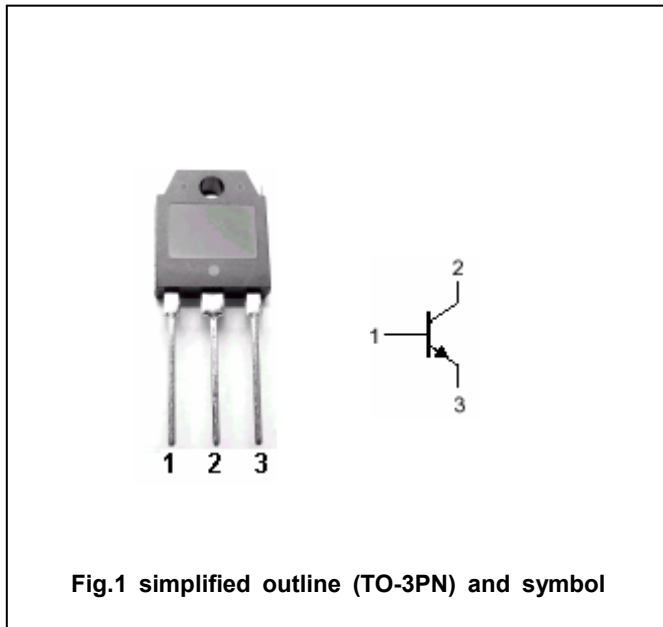
- With TO-3PN package
- High speed switching
- High V_{CBO}
- Low saturation voltage

APPLICATIONS

- For high voltage,high speed power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_B	Base current		5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	100	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon NPN Power Transistors

2SC2749

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =10mA ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =400V I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			100	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15		80	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	8			

PACKAGE OUTLINE

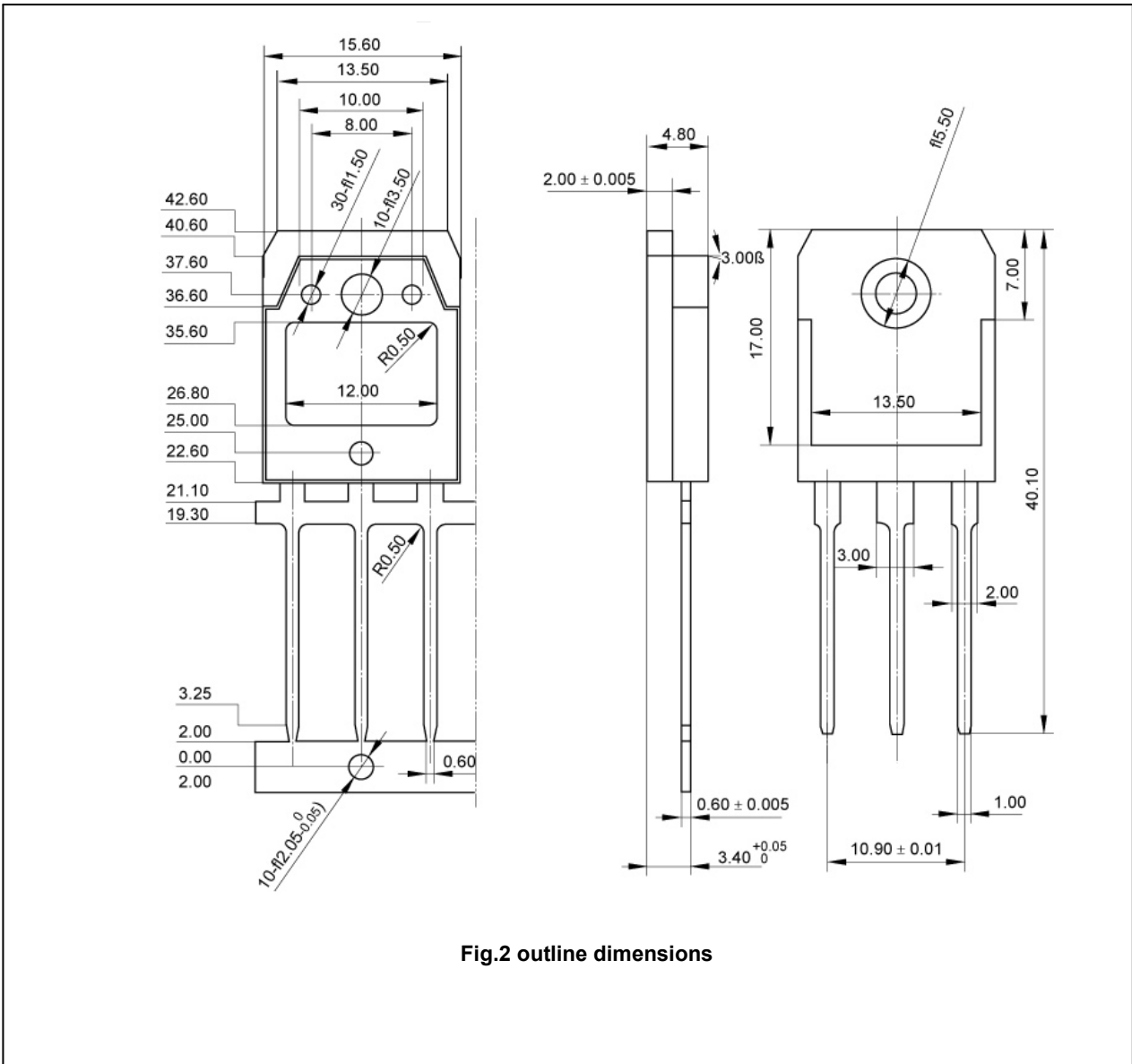


Fig.2 outline dimensions